

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Please amend claims 1, 7, 11, 14 and 16-18, and cancel claims 4 and 19-36 as follows:

1. (Currently Amended) A method of fabricating a suspended microstructure with a sloped support, comprising the steps of:

(a) providing a member having three stacked up layers including a first substrate layer, a second temporary layer and a third photoresist layer;

(b) photolithographically transferring a sloped pattern to the third photoresist layer by means of a grey scale mask;

(c) etching the second layer through the third layer resulting from step (b) to obtain a surface with at least one continuous slope with a predetermined angle with respect to the first substrate layer;

(d) depositing a fourth layer on the previous layers;

(e) etching the fourth layer to obtain the sloped support; and

(f) (i) depositing a fifth planarization layer for covering the previous layers except for a top portion of the sloped support;

(ii) depositing a sixth layer on the previous layers; and

(iii) etching the sixth layer to obtain a suspended microplatform;

(g) removing the second layer and the fifth layer to obtain the suspended microstructure with the sloped support.

2. (Original) A method according to claim 1, wherein:

the etching of step (c) is performed in such a way that the surface that is obtained includes a plateau with two opposite continuous slopes each having a predetermined angle with respect to the first substrate layer.

3. (Original) A method according to claim 2, wherein the predetermined angles are substantially equal.

4. Cancelled.

5. (Original) A method according to claim 1, wherein the depositing of step (d) is performed by means of a plasma-enhanced chemical vapor deposition technique.

6. (Original) A method according to claim 1, wherein the removing of step (f) is performed by means of a plasma isotropic etching technique or a wet etching technique.

7. (Currently Amended) A method according to claim 4 1, wherein the removal of the fifth layer is performed by means of a plasma isotropic etching technique or a wet etching technique.

8. (Original) A method according to claim 1, wherein the fourth layer of step (d) is made of a material selected from the group including SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Ti, Al, V, Au and Si.

9. (Original) A method according to claim 1, wherein the depositing of step (d) is performed by means of a technique selected from the group including sputtering technique, resistive evaporation technique and electroplating technique.

10. (Original) A method according to claim 1, wherein the etching of step (c) or (e) is performed by means of a reactive ion etching technique or a wet etching technique.

11. (Currently Amended) A method according to claim 4 1, wherein the depositing step (ii) is performed by means of a plasma-enhanced chemical vapor deposition technique.
12. (Original) A method according to claim 1, wherein the second temporary layer of step (a) is made of a polymer or made of glass.
13. (Original) A method according to claim 12, wherein the polymer is polyimide.
14. (Currently Amended) A method according to claim 4 1, wherein the fifth planarization layer of step (i) is made of a polymer or made of glass.
15. (Previously Presented) A method according to claim 14, wherein the polymer is polyimide.
16. (Currently Amended) A method according to claim 4 1, wherein the sixth layer of step (ii) is made of a material selected from the group including SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Ti, Al, V, Au and Si.
17. (Currently Amended) A method according to claim 4 1, wherein the depositing of step (ii) is performed by means of a technique selected from the group including sputtering technique, resistive evaporation technique and electroplating technique.
18. (Currently Amended) A method according to claim 4 1, wherein the etching of step (iii) is performed by means of a reactive ion etching technique or a wet etching technique.
- 19-36. (Cancelled)